

Dmitry Donetsky

List of Publications by Year in descending order

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13
papers

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citations

1040056

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13
docs citations

13
times ranked

268
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrical modulation of the LWIR absorption and refractive index in InAsSb-based strained layer superlattice heterostructures. Journal of Applied Physics, 2020, 128, 083101.	2.5	3
2	Perspective on advances in InAsSb type II superlattices grown on virtual substrates. Applied Physics Letters, 2020, 117, .	3.3	3
3	Materials design parameters for infrared device applications based on III-V semiconductors. Applied Optics, 2017, 56, B58.	2.1	15
4	Development of Bulk InAsSb Alloys and Barrier Heterostructures for Long-Wave Infrared Detectors. Journal of Electronic Materials, 2015, 44, 3360-3366.	2.2	27
5	Structural and Optical Characteristics of Metamorphic Bulk InAsSb. International Journal of High Speed Electronics and Systems, 2014, 23, 1450021.	0.7	0
6	Transport properties of holes in bulk InAsSb and performance of barrier long-wavelength infrared detectors. Semiconductor Science and Technology, 2014, 29, 112002.	2.0	7
7	Metamorphic InAsSb-based barrier photodetectors for the long wave infrared region. Applied Physics Letters, 2013, 103, .	3.3	30
8	Metamorphic InAsSb/AlInAsSb heterostructures for optoelectronic applications. Applied Physics Letters, 2013, 102, .	3.3	28
9	Conduction- and Valence-Band Energies in Bulk $\text{InAs}_{1-x}\text{Sb}_x$ and Type-II $\text{InAs}_{1-x}\text{Sb}_x/\text{InAs}$ Strained-Layer Superlattices. Journal of Electronic Materials, 2013, 42, 918-926.	2.2	26
10	Unrelaxed bulk InAsSb with novel absorption, carrier transport, and recombination properties for MWIR and LWIR photodetectors. Proceedings of SPIE, 2012, , .	0.8	9
11	Minority carrier lifetime in type-2 InAs/GaSb strained-layer superlattices and bulk HgCdTe materials. Applied Physics Letters, 2010, 97, .	3.3	109
12	Carrier lifetime measurements in short-period InAs/GaSb strained-layer superlattice structures. Applied Physics Letters, 2009, 95, .	3.3	124
13	Effect of Quantum Well Compressive Strain Above 1% On Differential Gain and Threshold Current Density in Type-I GaSb-Based Diode Lasers. IEEE Journal of Quantum Electronics, 2008, 44, 1204-1210.	1.9	26